

Serial No. 10/824,417  
Amdt. dated April 22, 2008  
Reply to Office Action of January 22, 2008

Docket No. YHK-0111

**Amendments to the Specification**

Please amend Paragraph [81] as follows:

Preferably, first to fourth switches Q1 to Q4 are sequentially turned on to thereby control a flow of current. A diode is connected, in parallel, to each of the first to fourth switches Q1 to Q4. The diodes can be used as internal diodes of the first to fourth switches Q1 to Q4. Alternatively, the diodes may be used as external diodes thereof. Each of the first to fourth switches Q1 to Q4 employs any one of semiconductor switching devices such as a metal oxide semiconductor field-effect transistor (MOSFET), an insulated gate bipolar transistor (IGBT), a silicon-controlled rectifier (SCR), a bipolar junction transistor (BJT) and a high electron mobility transistor (HEMT), etc. Further, other switches and/or configurations are possible, which are illustrated in co-pending U.S. application Ser. Nos. 10/416,286 filed May 9, 2003, (OP3095) 10/743,289 filed December 23, 2003 [[\_\_\_\_\_]], and (OP3096) 10/743,284 filed December 23, 2003 [[\_\_\_\_\_]], assigned to the same Assignee, whose entire disclosure is incorporated herein by reference.